



ENGINEERING PHYSICS

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Class # 52

- **Giant Magneto Resistance effect**
- **Applications of GMR effect**
 - **Memory-storage device**
 - **Other applications**

ENGINEERING PHYSICS

Unit 5 : Applications of Magnetic materials



➤ *Suggested Reading*

1. *The Science and Engineering of Materials* by Donald

R. Askeland, Pradeep P. Fulay, Wendelin J. Wright, 6th

edition, Ch 20, 2011.

2. *Learning material prepared by the Department of Physics,*

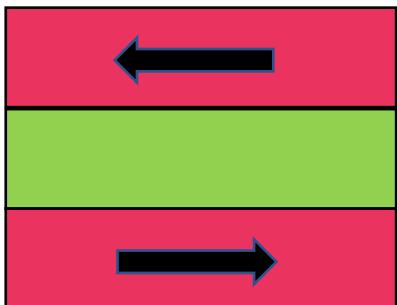
PESU

➤ *Reference Videos*

<https://nptel.ac.in/courses/115/105/115105122/>

Giant Magneto Resistance effect

- *Quantum mechanical magneto resistance effect*
 - *Observed in layered magnetic materials*
 - *Significant change in resistance to the current flow.*
 - *Spin scattering of electrons*
-



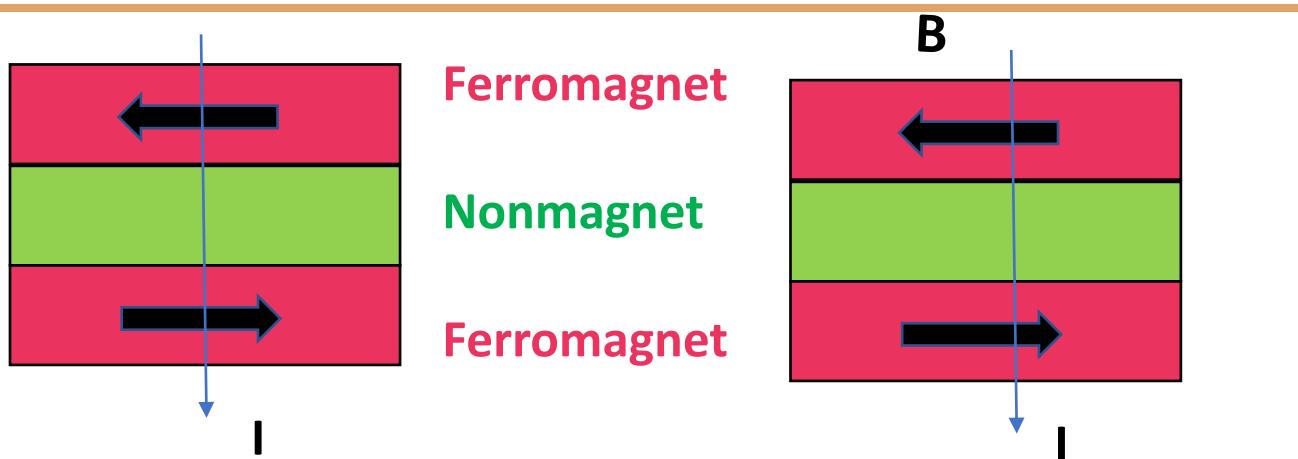
Ferromagnet

Non magnet

Ferromagnet

Giant Magneto Resistance effect

- *Antiparallel magnetisation – high resistance*
- *Parallel magnetization - low resistance*
- *Magnetisation direction can be controlled by applying an external field.*



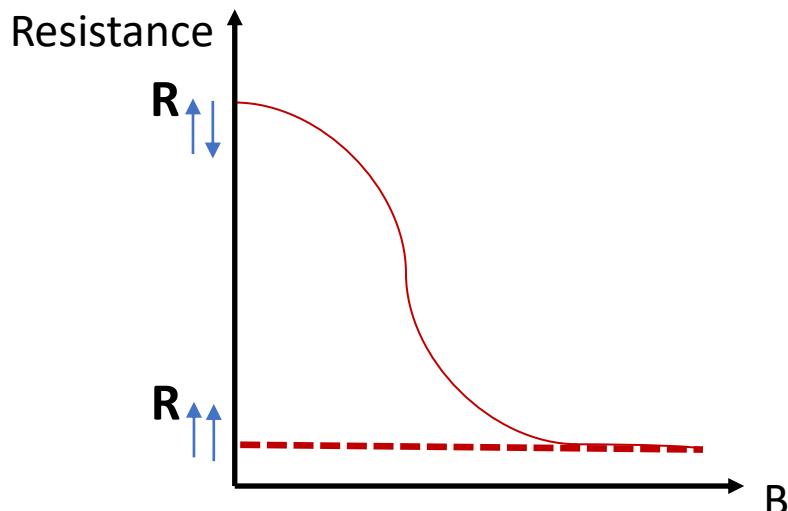
Antiparallel Magnetisation

Parallel Magnetisation

Giant Magneto Resistance effect

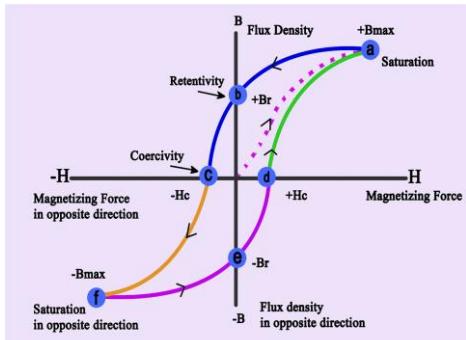
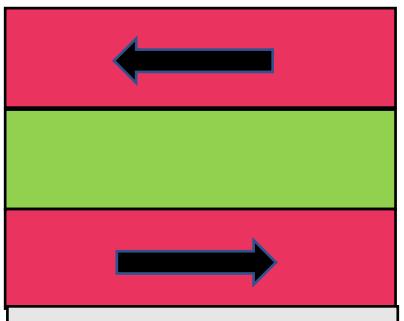
$$GMR = \frac{R_{\uparrow\downarrow} - R_{\uparrow\uparrow}}{R_{\uparrow\uparrow}}$$

- *Depends on many parameters such as the geometry of the device, temperature and thickness of ferromagnetic and non-magnetic layers.*



Giant Magneto Resistance effect

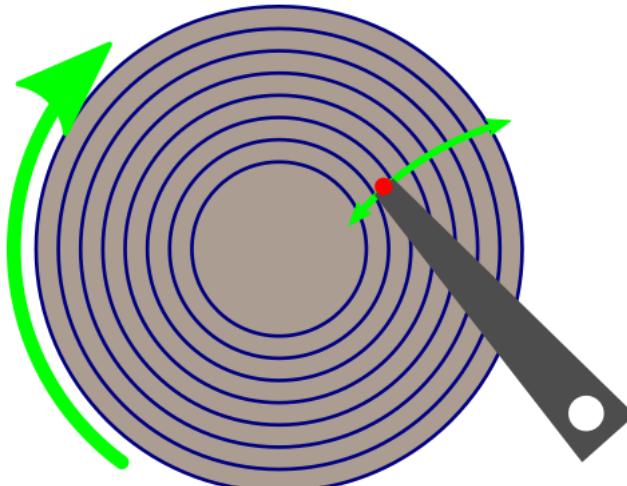
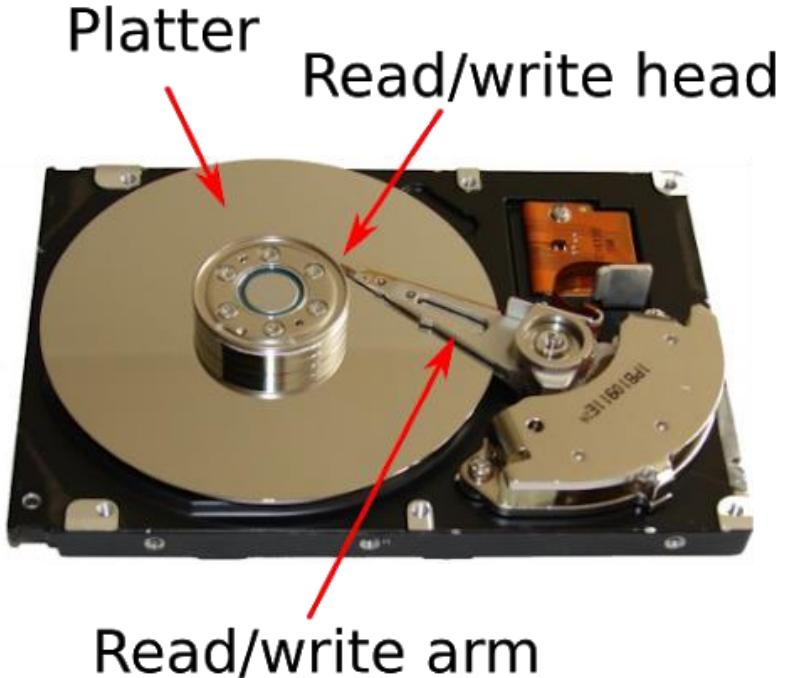
- *magnetic layers - 3-5nm and non-magnetic layer - 25nm*
observed change in resistance is as high as 50% of which is significant for any practical measurements and applications.
- *GMR effect can be enhanced by using spin filters - certain spin orientation.*



Applications
read head of magnetic memories, biosensors, etc.

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GMR effect - Applications

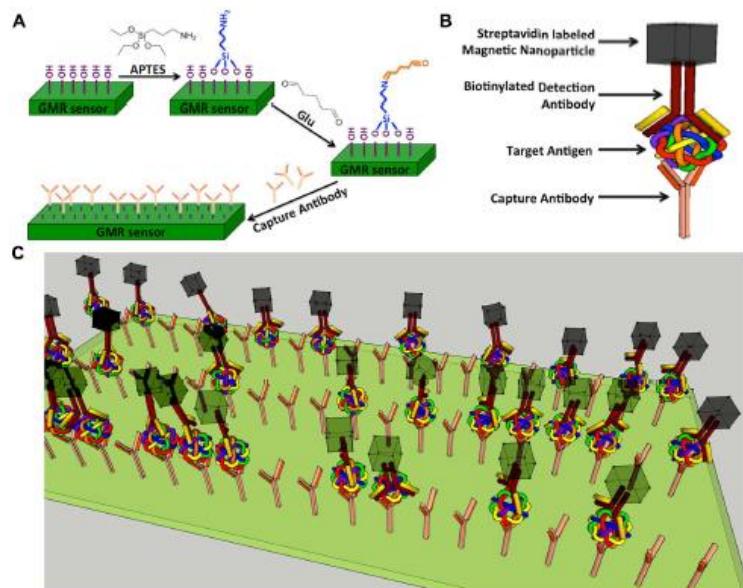


Hard disk drive

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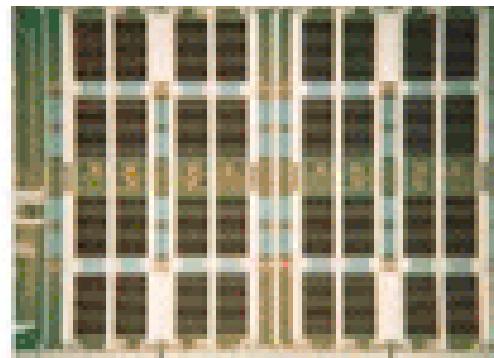
GMR effect - Applications

Biosensor



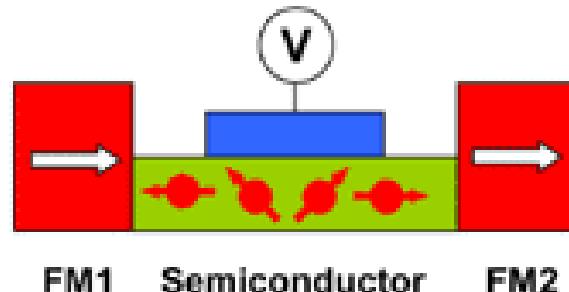
Venkatramana D. Krishna et al., *Frontiers in Microbiology*, doi: 10.3389/fmicb.2016.00400

MRAM



M Johnson et al., *IEEE Spectrum*, 37,33, 2000

Spin-FET



S Datta et al., *Applied Physics Letters*, 56, 665, 1990

Magnetic permeability & susceptibility

Origin of magnetism

- Orbital and spin angular momenta
- Larmor precession

Classification of magnetic materials

Diamagnetic materials

Paramagnetic materials

- Quantum theory of paramagnetism
- Classical theory of paramagnetism
- Curie's law
- Weiss molecular field theory

Ferromagnetic materials

- Ferromagnetism
- Anti-ferromagnetism
- Ferrimagnetism

Giant Magneto Resistance – (GMR effect)

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List of Formulae

$$B = \frac{\phi}{A}$$

$$E_m = \mu \cdot B$$

$$M = \chi_m H$$

$$B = \mu H$$

$$\mu = \mu_o \mu_r$$

$$H = \frac{nI}{l}$$

$$\mu_r = (1 + \chi_m)$$

$$B = \mu_o (H + M)$$

$$\mu = IA$$

$$\omega_L = \frac{e}{2m_e} B$$

$$\chi \propto \frac{1}{T}$$

$$\chi = \frac{C}{T - T_c}$$

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Numericals

1. An iron rod of length **0.5m** has a cross sectional area of **$4 \times 10^{-4} \text{ m}^2$** .

If the flux of magnetic induction through the bar is **2×10^{-4} Weber** and relative permeability of iron is **1000**, calculate

- a. Magnetic susceptibility
- b. Intensity of magnetising field
- c. Magnetisation

Solution: Given: $\phi = 2 \times 10^{-4}$ Weber

$$A = 4 \times 10^{-4} \text{ m}^2$$

$$L = 0.5\text{m}$$

$$\mu_r = 1000$$

To find: $\chi_m = ?$

$$H = ?$$

$$M = ?$$

a. Magnetic susceptibility $\chi_m = (\mu_r - 1)$
 $= 1000 - 1 = 999$

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Numericals

b. Intensity of magnetising field $H = \frac{B}{\mu} = \frac{B}{\mu_0 \mu_r}$

Since, $B = \frac{\emptyset}{A}$ $\mu = \mu_0 \mu_r$ $H = \frac{\emptyset/A}{\mu_0 \mu_r}$

Substituting the values and simplifying, we get, $H = 398.09 \text{ A/m}$

c. Magnetisation $M = \chi_m H = 999 \times 398.09$

$M = 397.7 \text{ A/m}$

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Numericals

2. A magnetic field of 1T is applied to an electron undergoing orbital motion. Calculate the precessional frequency.

Solution: Given: $B = 1 \text{ T}$

To find: $\omega_L = ?$

$$\omega_L = \frac{e}{2m_e} B = \frac{1.6 \times 10^{-19}}{2 \times 9.1 \times 10^{-31}} \times 1$$

$$\omega_L = 87.8 \times 10^9 \text{ rad/s}$$

The concepts which are correct are....

1. GMR effect is observed only in 3 layered magnetic materials.
2. Change in resistance due to magnetization is temperature dependent
3. Scattering of electrons is less in the case of parallel magnetization.
4. Electron spin orientation is fixed in the free layer of magnetic material
5. Resistance increases when spin state of the two layers are antiparallel.



THANK YOU

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